

# FDG8850NZ

## Dual N-Channel PowerTrench® MOSFET

30V, 0.75A, 0.4Ω

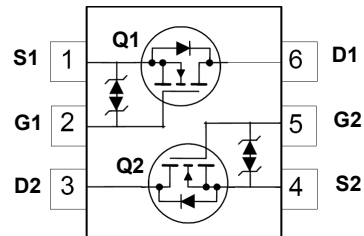
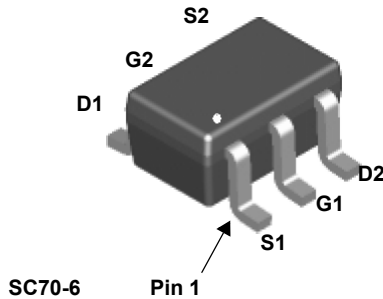
### Features

- Max  $r_{DS(on)}$  = 0.4Ω at  $V_{GS} = 4.5V$ ,  $I_D = 0.75A$
- Max  $r_{DS(on)}$  = 0.5Ω at  $V_{GS} = 2.7V$ ,  $I_D = 0.67A$
- Very low level gate drive requirements allowing operation in 3V circuits ( $V_{GS(th)} < 1.5V$ )
- Very small package outline SC70-6
- RoHS Compliant



### General Description

This dual N-Channel logic level enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs. Since bias resistors are not required, this dual digital FET can replace several different digital transistors, with different bias resistor values.



### MOSFET Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units	
$V_{DS}$	Drain to Source Voltage	30	V	
$V_{GS}$	Gate to Source Voltage	$\pm 12$	V	
$I_D$	Drain Current -Continuous	0.75	A	
	-Pulsed	2.2		
$P_D$	Power Dissipation for Single Operation	(Note 1a)	0.36	W
		(Note 1b)	0.30	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$	

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1a)	350	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1b)	415	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.50	FDG8850NZ	7"	8mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		25		$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$			$\pm 10$	$\mu\text{A}$

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	0.65	1.0	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-3.0		$\text{mV}/^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 4.5\text{V}, I_D = 0.75\text{A}$ $V_{GS} = 2.7\text{V}, I_D = 0.67\text{A}$ $V_{GS} = 4.5\text{V}, I_D = 0.75\text{A}, T_J = 125^\circ\text{C}$		0.25 0.29 0.36	0.4 0.5 0.6	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 0.75\text{A}$		3		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		90	120	pF
$C_{oss}$	Output Capacitance			20	30	pF
$C_{rss}$	Reverse Transfer Capacitance			15	25	pF

**Switching Characteristics (note 2)**

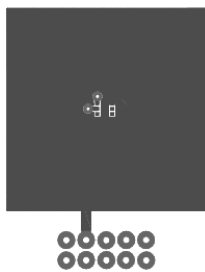
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 5\text{V}, I_D = 0.5\text{A},$ $V_{GS} = 4.5\text{V}, R_{GEN} = 6\Omega$		4	10	ns
$t_r$	Rise Time			1	10	ns
$t_{d(off)}$	Turn-Off Delay Time			9	18	ns
$t_f$	Fall Time			1	10	ns
$Q_g$	Total Gate Charge			1.03	1.44	nC
$Q_{gs}$	Gate to Source Charge		$V_{GS} = 4.5\text{V}, V_{DD} = 5\text{V}, I_D = 0.75\text{A}$		0.29	
$Q_{gd}$	Gate to Drain "Miller" Charge			0.17		nC

**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current			0.3	A	
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 0.3\text{A}$ (Note 2)		0.76	1.2	V

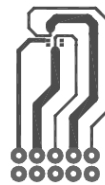
**Notes:**

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



Scale 1:1 on letter size paper.

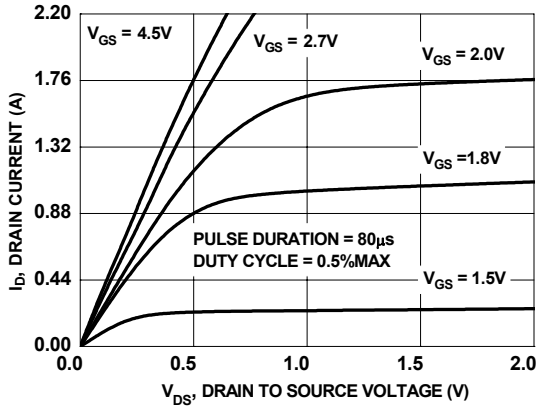
a.  $350^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper.



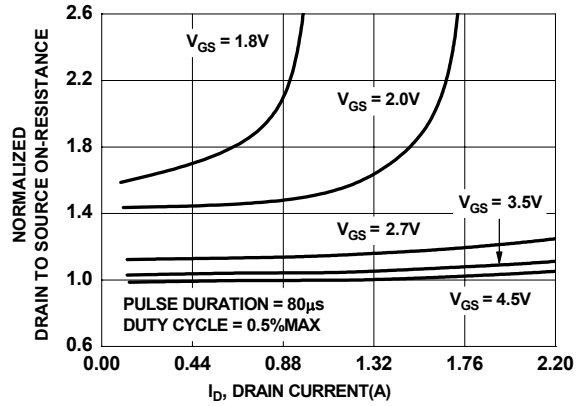
b.  $415^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

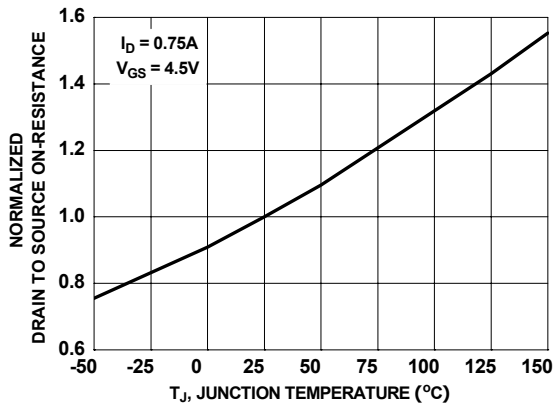
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



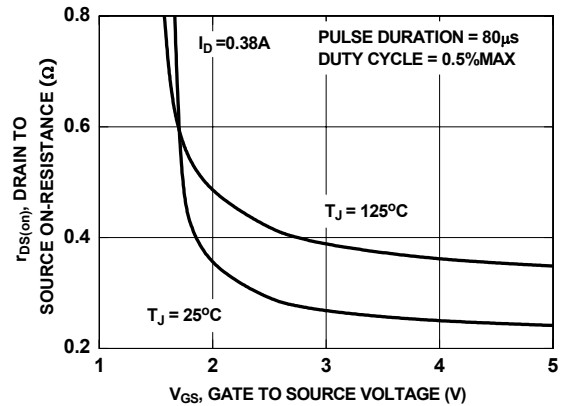
**Figure 1. On-Region Characteristics**



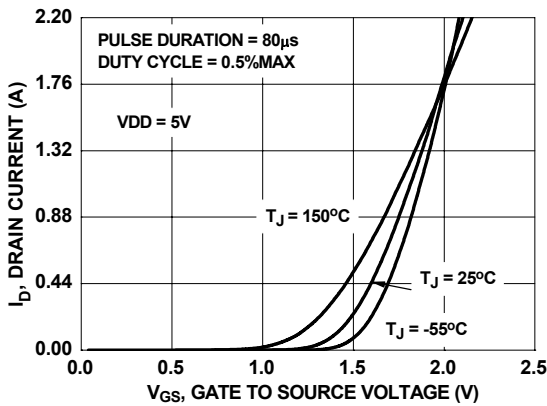
**Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage**



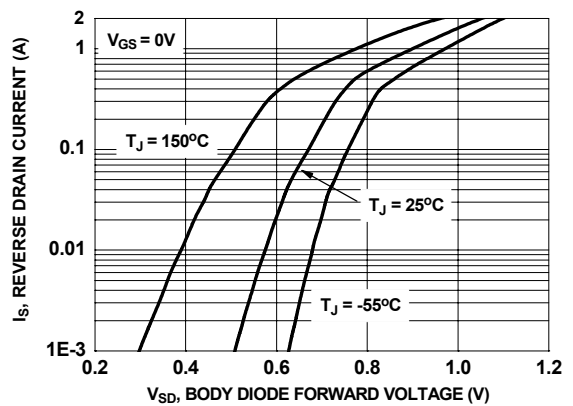
**Figure 3. Normalized On-Resistance vs Junction Temperature**



**Figure 4. On-Resistance vs Gate to Source Voltage**

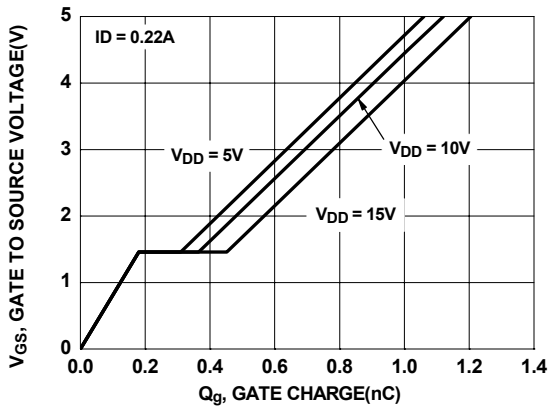


**Figure 5. Transfer Characteristics**

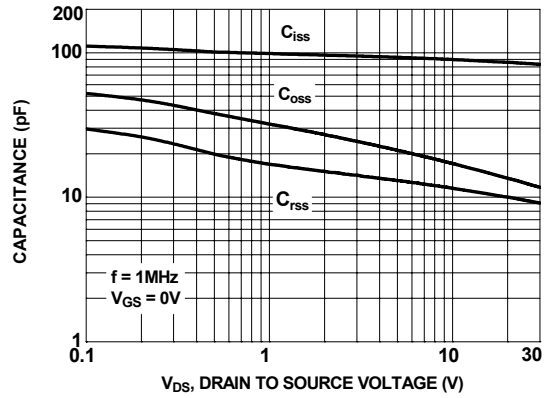


**Figure 6. Source to Drain Diode Forward Voltage vs Source Current**

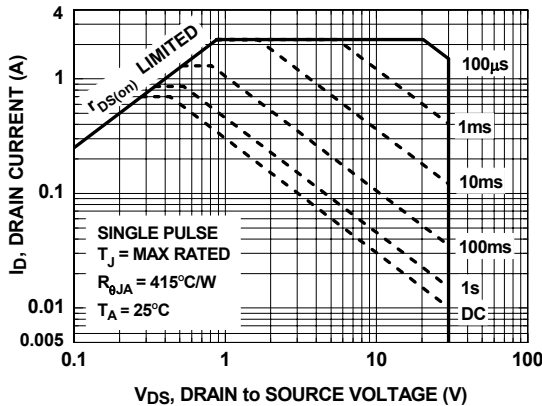
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



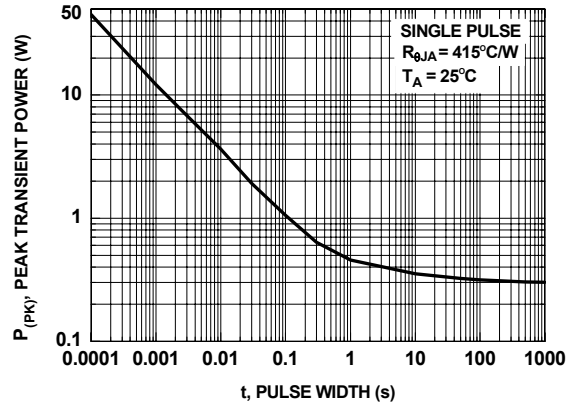
**Figure 7. Gate Charge Characteristics**



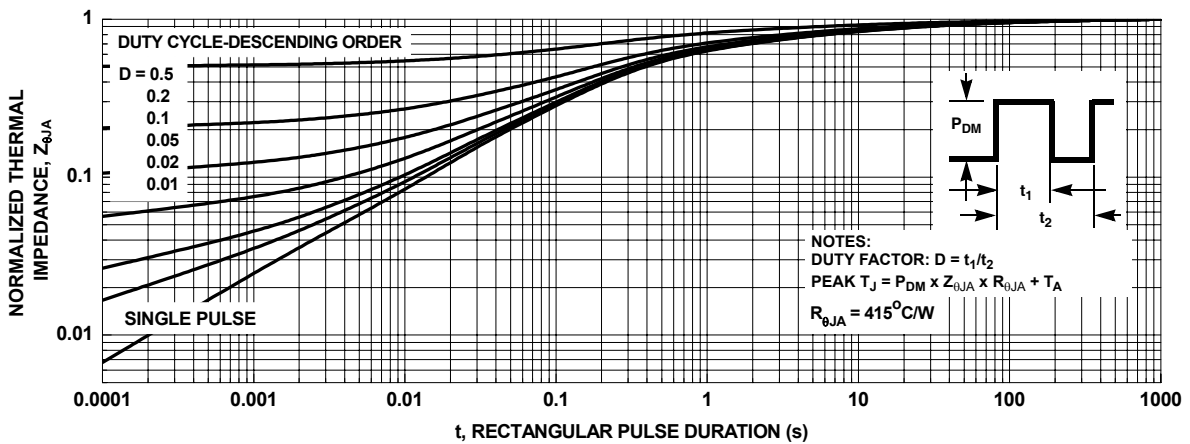
**Figure 8. Capacitance vs Drain to Source Voltage**



**Figure 9. Forward Bias Safe Operating Area**



**Figure 10. Single Pulse Maximum Power Dissipation**




**Figure 11. Transient Thermal Response Curve**



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